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# **HRU0103A**

Silicon Schottky Barrier Diode for Rectifying

**HITACHI**

ADE-208-450 (Z)  
Rev 0  
June 1996

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## **Features**

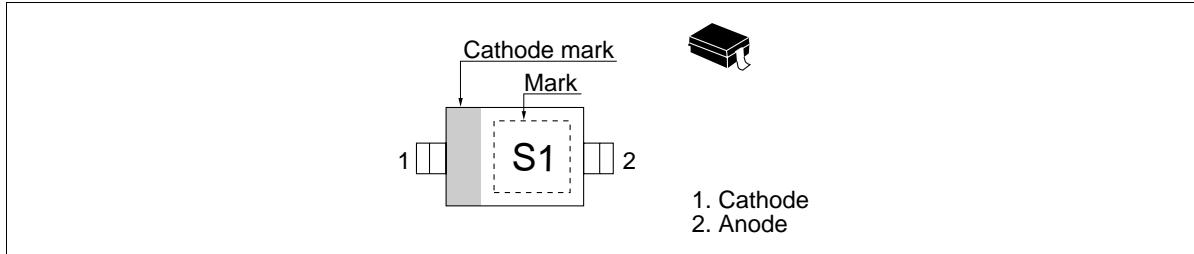
- Low forward voltage drop and suitable for high efficiency forward current.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

## **Ordering Information**

Type No.	Laser Mark	Package Code
HRU0103A	S1	URP

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## **Outline**



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## HRU0103A

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### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	VRRM*1	30	V
Average rectified current	Io*2	100	mA
Non-Repetitive peak forward surge current	IFSM*3	3	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55~+150	°C

Note 1. See Fig.3

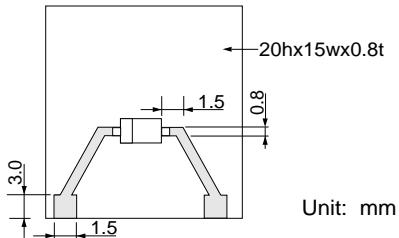
Note 2. See Fig.4

Note 3. 10msec sine wave 1 pulse

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	VF	~	~	0.44	V	IF = 100 mA
Reverse current	IR	~	~	50	μA	VR = 30V
Thermal resistance	Rth(j-a)	~	600	~	°C/W	Polyimide substrate*1

Note 1. Polyimide PCB



## Main Characteristic

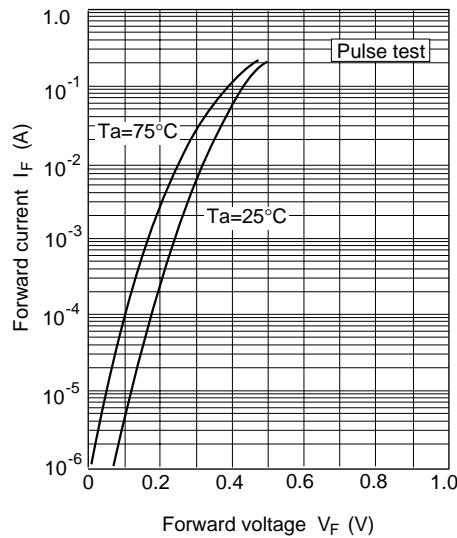


Fig.1 Forward current Vs. Forward voltage

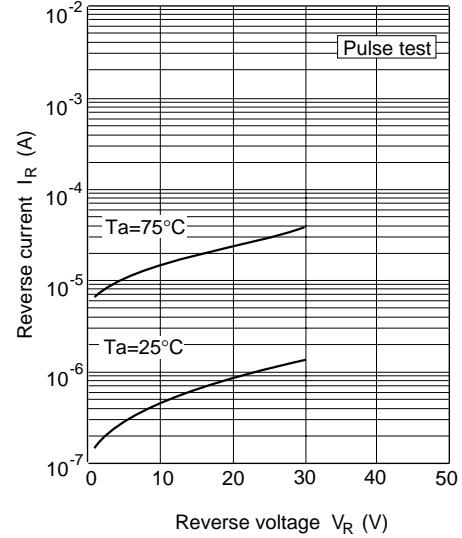


Fig.2 Reverse current Vs. Reverse voltage

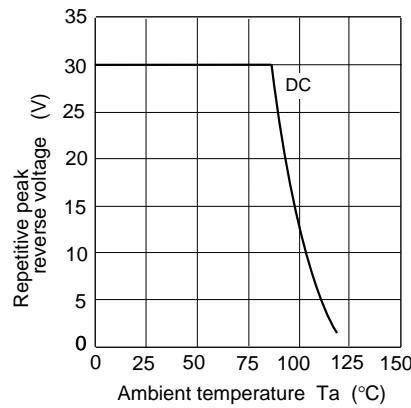


Fig.3 Repetitive peak reverse voltage Vs. Ambient temperature

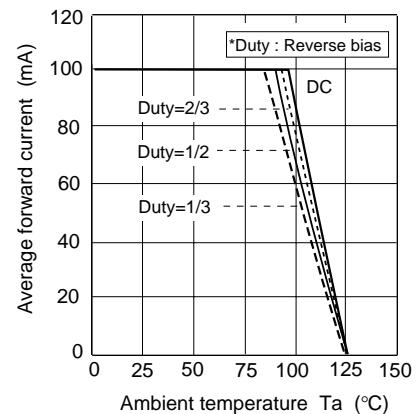


Fig.4 Average forward current Vs. Ambient temperature

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### Package Dimensions

Unit : mm

